Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	5	"6654275"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 09:29
S10	2	("20020131294").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 11:38
S7	12	("5304502"|"5771196"|"5950219"|"6104045"|"6128216"|"6275433").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 13:36
S2	2	("6654275").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 14:12
S3	1927	(365/154).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 13:32
S4	3162	(365/189.01).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 13:32
S5	1816	(365/189.09).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 13:33
S6	1106	(365/189.11).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/06 13:33
S12	123	(365/199).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 11:55
L2	1278	(increas$3 increment$3) near5 (voltage potential) near5 (row column word bit) adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 09:30

L3	184	(increas$3 increment$3) near5 (voltage potential) near5 (row column word bit) adj line with threshold	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:04
L11	4	(increas$3 increment$3) near5 (voltage potential) near5 (row column word bit) adj line with threshold same ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:04
L1	10599	(increas$3 increment$3) same (voltage potential) same (row column word bit) adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:03
S8	102	(variable adjust$4 vary$3 varied) near5 (voltage potential) near5 (row word) adj line same (bit column) adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:16
L4	64	3 and SRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 09:59
L5	142	3 same (memory cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:33
L12	93	3 same (memory cell) same (read$3 writ$3 program$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:33
L6	24	3 same (sram dram)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 09:31
L7	8	3 same SRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:02
L8	2314	ferroelectric same threshold	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:02

L10	797	ferroelectric same threshold near3 (potential voltage) same (cell memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:03
L9	1148	ferroelectric same threshold same (cell memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:03
L13	21	numata.in. and mram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:33
S9	14	S8 and sram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 14:16
S11	15	sram same read$3 adj pulse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 11:55